

DESCRIPTION

The HY638100 is a high-speed 131,072 x 8-bits CMOS static RAM fabricated using Hyundai's high performance CMOS process technology. This high reliability process coupled with high-speed circuit design techniques, yields maximum access time of 15ns. The HY638100 has a data retention mode that guarantees data to remain valid at a minimum power supply voltage of 2.0 volt. It is suitable for use in high-density high-speed system applications.

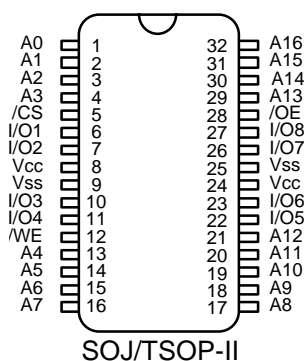
FEATURES

- Single 5V±10% Power Supply
- High speed - 15/20/25ns(max.)
- Low power consumption(Max.)

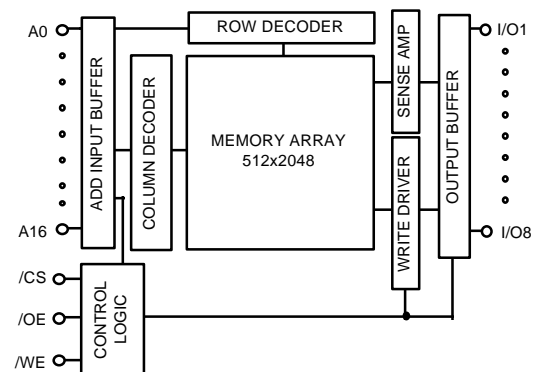
Mode	Conditions	Current	Units	
Operating	15ns	150	mA	
	20/25ns	140	mA	
Standby	TTL	40	mA	
	CMOS		2	mA
		L	500	uA

- Battery backup(L-part)
- 2.0V(min.) data retention
- Fully static operation and Tri-state outputs
- No clock or refresh required
- TTL compatible inputs and outputs
- Standard pin configuration
 - 32pin 400mil SOJ
 - 32pin 400mil TSOP-II

PIN CONNECTION



BLOCK DIAGM



PIN DESCRIPTION

Pin Name	Pin Function
/CS	Chip Select
/WE	Write Enable
/OE	Output Enable
A0~A16	Addresss Input
I/O1~I/O8	Data Input/Output
Vcc	Power(+5.0V)
Vss	Ground

ORDERING INFORMATION

Part No.	Speed	Power	Package
HY638100J	15/20/25		SOJ
HY638100LJ	15/20/25	L-part	SOJ
HY638100T2	15/20/25		TSOP-II
HY638100LT2	15/20/25	L-part	TSOP-II

ABSOLUTE MAXIMUM RATING (1)

Symbol	Parameter	Rating	Unit
VCC, VIN, VOUT	Power Supply, Input/Output Voltage	-0.5 to 7.0	V
TA	Operating Temperature	0 to 70	°C
TSTG	Storage Temperature	-65 to 150	°C
PD	Power Dissipation	1.0	W
IOUT	Data Output Current	50	mA
TSOLDER	Lead Soldering Temperature & Time	260 • 10	°C • sec

Note

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational of this specification is not implied. Exposure to absolute maximum rating conditions for extended period may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS

TA=0°C to 70°C

Symbol	Parameter	Min.	Typ	Max.	Unit
VCC	Supply Voltage	4.5	5.0	5.5	V
VSS	Ground	0	0	0	V
VIH	Input High Voltage	2.2	-	Vcc+0.5	V
VIL	Input Low Voltage	-0.5(1)	-	0.8	V

Note

1. VIL = -3.0V for pulse width less than 10ns

TRUTH TABLE

/CS	/WE	/OE	Mode	I/O Operation
H	X	X	Standby	Hi-Z
L	H	H	Output Disabled	Hi-Z
L	H	L	Read	DOUT
L	L	X	Write	DIN

Note:

1. H=VIH, L=VIL, X=Don't care

DC ELECTRICAL CHARACTERISTICS

V_{CC} = 5.0V±10%, T_A = 0°C to 70°C, unless otherwise specified.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit	
IIL	Input Leakage Current	V _{SS} ≤ V _{IN} ≤ V _{CC}	-2	-	2	uA	
ILO	Output Leakage Current	V _{SS} ≤ V _{OUT} ≤ V _{CC} , /CS = V _{IH} or /OE = V _{IH} or /WE = V _{IL}	-2	-	2	uA	
ICC1	Average Operating Current	/CS = V _{IL} , I/I/O = 0mA, Min. Duty Cycle = 100%	15ns	-	-	150	mA
			20/25ns	-	-	140	mA
ISB	TTL Standby Current (TTL Inputs)	/CS = V _{IH} , V _{IN} =V _{IH} or V _{IL} Min. Cycle	-	-	40	mA	
ISB1	CMOS Standby Current (CMOS Inputs)	/CS ≥ V _{CC} -0.2V, V _{IN} ≥ V _{CC} -0.2V or V _{IN} ≤ 0.2V		-	-	2	mA
			L	-	50	500	uA
VOL	Output Low Voltage	IOL = 8.0mA	-	-	0.4	V	
VOH	Output High Voltage	IOH = -4.0mA	2.4	-	-	V	

Note : Typical values are at V_{CC} = 5.0V, T_A = 25°C

AC CHARACTERISTICS

V_{CC} = 5.0V±10%, T_A = 0°C to 70°C, unless otherwise specified.

#	Symbol	Parameter	-15		-20		-25		Unit
			Min	Max	Min	Max	Min	Max	
READ CYCLE									
1	TRC	Read Cycle Time	15	-	20	-	25	-	ns
2	TAA	Address Access Time	-	15	-	20	-	25	ns
3	TACS	Chip Select Access Time	-	15	-	20	-	25	ns
4	TOE	Output Enable to Output Valid	-	7	-	9	-	10	ns
5	TCLZ	Chip Select to Output in Low Z	3	-	3	-	3	-	ns
6	TOLZ	Output Enable to Output in Low Z	3	-	3	-	3	-	ns
7	TCHZ	Chip Deselecting to Output in High Z	0	8	0	9	0	10	ns
8	TOHZ	Out Disable to Output in High Z	0	8	0	9	0	10	ns
9	TOH	Output Hold from Address Change	3	-	3	-	3	-	ns
WRITE CYCLE									
10	TWC	Write Cycle Time	15	-	20	-	25	-	ns
11	TCW	Chip Select to End of Write	12	-	15	-	17	-	ns
12	tAW	Address Valid to End of Write	12	-	15	-	17	-	ns
13	tAS	Address Set-up Time	0	-	0	-	0	-	ns
14	tWP	Write Pulse Width	12	-	15	-	17	-	ns
15	tWR	Write Recovery Time	2	-	2	-	2	-	ns
16	tWHZ	Write to Output in High Z	0	7	0	9	0	10	ns
17	tDW	Data to Write Time Overlap	8	-	9	-	10	-	ns
18	tDH	Data Hold from Write Time	0	-	0	-	0	-	ns
19	tOW	Output Active from End of Write	3	-	3	-	3	-	ns

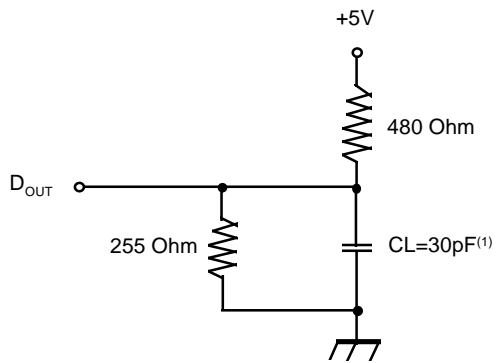
AC TEST CONDITIONS

V_{CC} = 5.0V±10%, T_A = 0°C to 70°C, unless otherwise specified.

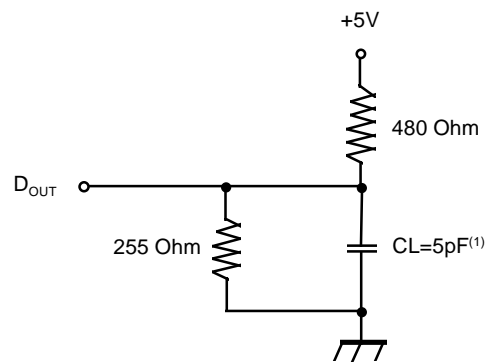
Parameter	Value
Input Pulse Level	0V to 3.0V
Input Rise and Fall Time	3ns
Input and Output Timing Reference Level	1.5V
Output Load	See below

AC TEST LOADS

Output Load (A)



Output Load (B)
(for t_{CHZ}, t_{CLZ}, t_{OHZ}, t_{OLZ}, t_{WHZ} & t_{OW})



Note : Including jig and scope capacitance

CAPACITANCE

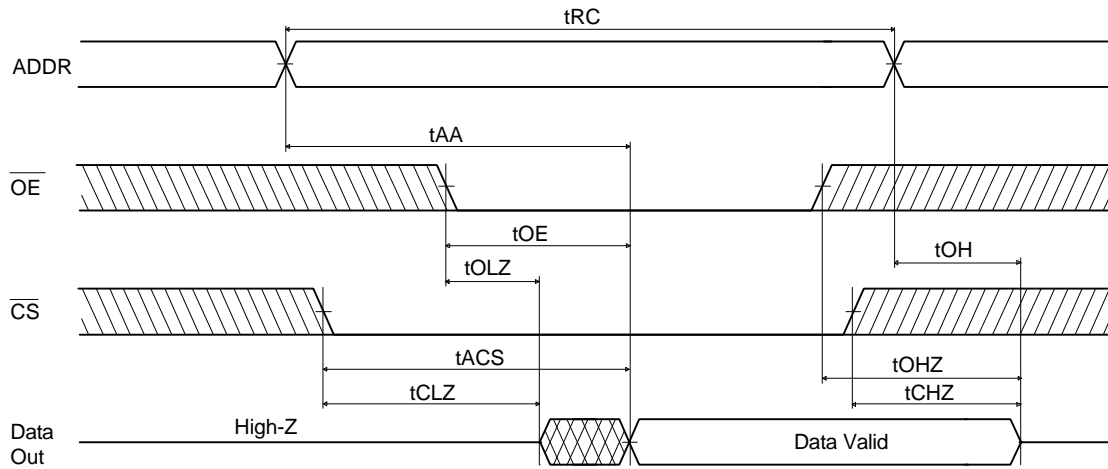
Temp = 25°C, f = 1.0MHz

Symbol	Parameter	Condition	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	6	pF
C _{I/O}	Input/Output Capacitance	V _{I/O} = 0V	8	pF

Note : This parameter is sampled and not 100% tested

TIMING DIAGRAM

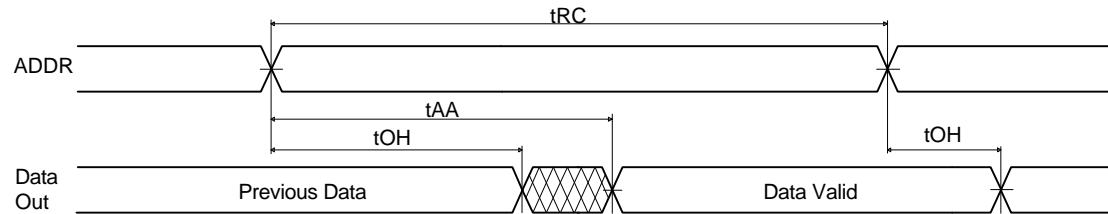
READ CYCLE 1



Note (Read Cycle)

1. t_{CHZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, t_{CHZ} max. is less than t_{CLZ} min. both for a given device and from device to device.
3. \overline{WE} is high for read cycle.

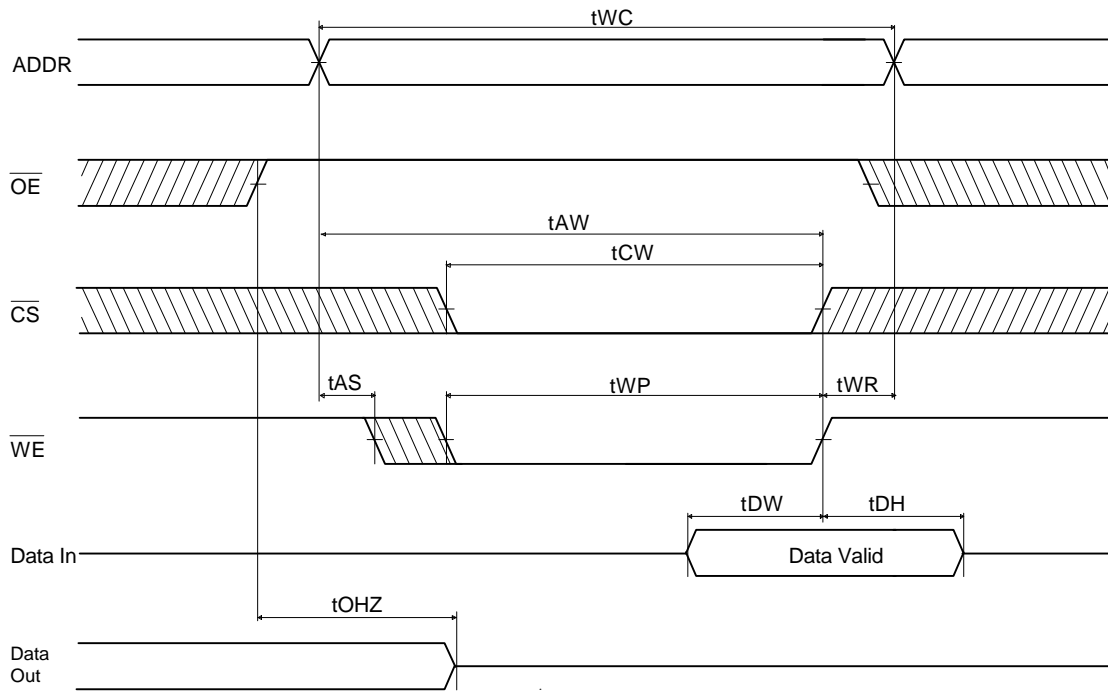
READ CYCLE 2



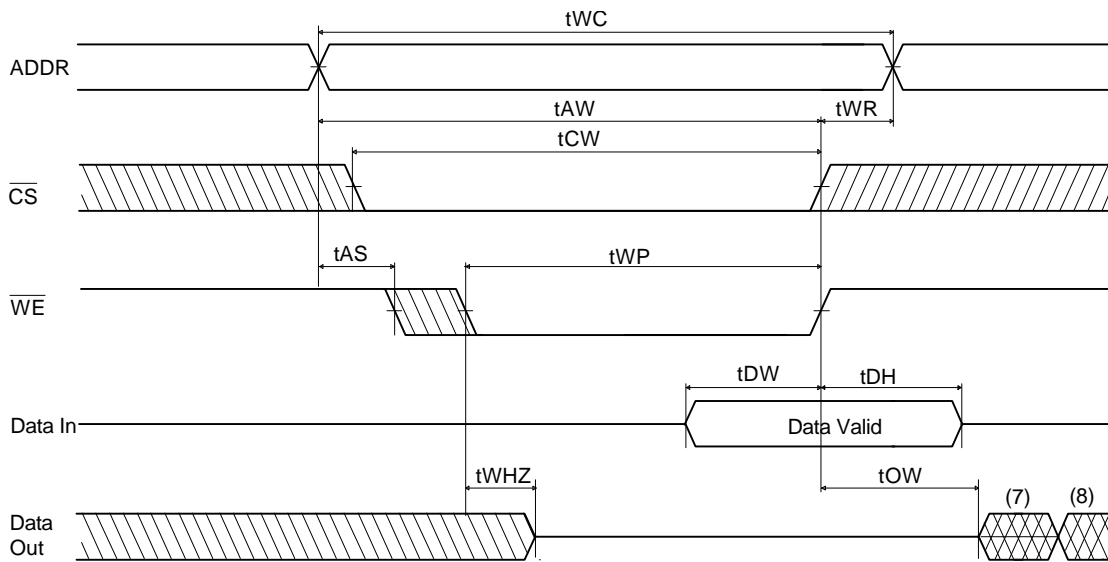
Note (Read Cycle)

1. \overline{WE} is high for read cycle.
2. Device is continuously selected $\overline{CS}=V_{IL}$.
3. $\overline{OE}=V_{IL}$.

WRITE CYCLE 1(/OE Clocked)



WRITE CYCLE 2(/OE Low Fixed)



Notes(Write Cycle)

1. A write occurs during the overlap of a low /CS and a low /WE. A write begins at the latest transition among /CS going low, and /WE going low : A write ends at the earliest transition among /CS going high and /WE going high. tWP is measured from the beginning of write to the end of write.
2. tCW is measured from the later of /CS going low to end of write.
3. tAS is measured from the address valid to the beginning of write.
4. tWR is measured from the end of write to the address change. tWR applied in case a write ends as /CS or /WE going high.
5. If /OE and /WE are in the read mode during this period, the I/O pins are in the output low-Z state, inputs of opposite phase of the output must not be applied because bus contention can occur.
6. If /CS goes low simultaneously with /WE going low or after /WE going low, the outputs remain in high impedance state.
7. DOUT is the same phase of latest written data in the write cycle.
8. DOUT is the read data of the new address.

DATA RETENTION ELECTRIC CHARACTERISTIC(L-Version)

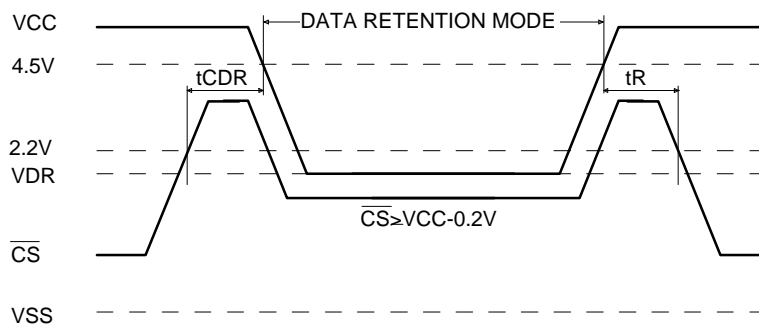
TA=0°C to 70°C

Symbol	Parameter	Test Conditions	Power	Min	Typ	Max	Unit
VDR	Vcc for Data Retention	/CS ≥ Vcc - 0.2V		2.0	-	-	V
ICCDR	Data Retention current	Vcc = 3V, /CS ≥ Vcc-0.2V Vin ≥ Vcc - 0.2 or ≤ 0.2V	L	-	10	50	uA
TCDR	Chip Deselect to Data Retention Time	See Data Retention Timing Diagram		0	-	-	ns
TR	Operating Recovery Time			tRC(2)	-	-	ns

Notes

1. Typical values are at the condition of TA=25°C
2. tRC is read cycle time

DATA RETENTION WAVEFORM

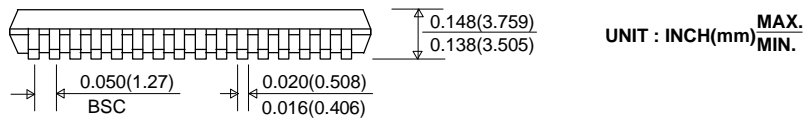
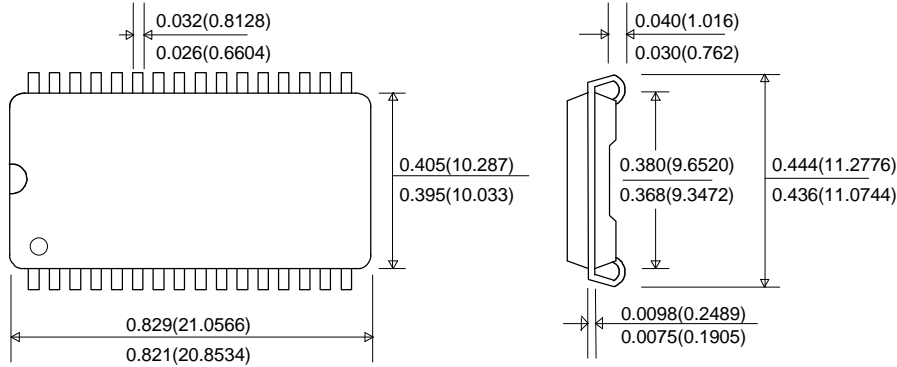


RELIABILITY SPEC.

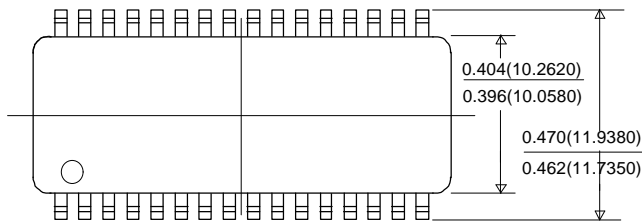
TEST MODE		TEST SPEC.
ESD	HBM	≥ 2000V
	MM	≥ 250V
LATCH - UP		≤ -100mA
		≥ 100mA

PACKAGE INFORMATION

32pin 400mil Small Outline J-Form Package (J)



32pin 400mil Thin Small Outline Package (T2)



UNIT : INCH(mm) **MAX.**
MIN.

